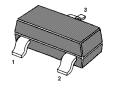
MMBT2907 / MMBT2907A PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into one group according to its DC current gain.



 Base 2.Emitter 3.Collector SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

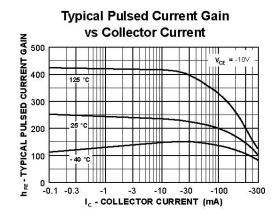
Parameter	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	60	V
Collector Emitter Voltage MMBT2907 MMBT2907A	-V _{CEO}	40 60	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	600	mA
Power Dissipation	P _{tot}	350	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

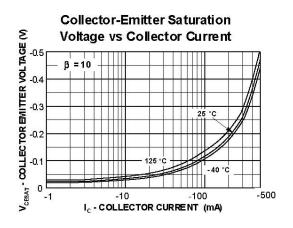
Page 1 of 4

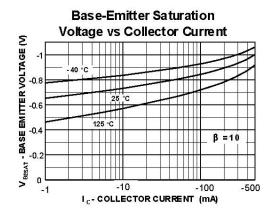
Characteristics at T_a = 25 °C

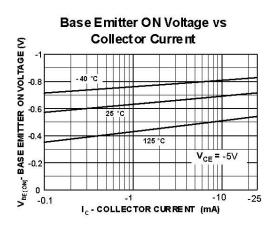
Parameter		Symbol	Min.	Max.	Unit
DC Current Gain at $-I_C = 0.1$ mA, $-V_{CE} = 10$ V	MMBT2907	h _{FE}	35	-	-
at $-I_C = 1 \text{ mA}, -V_{CE} = 10 \text{ V}$	MMBT2907A MMBT2907A	h _{FE} h _{FE}	75 50 100	-	-
at $-I_C = 10 \text{ mA}, -V_{CE} = 10 \text{ V}$	MMBT2907A MMBT2907 MMBT2907A	h _{FE} h _{FE} h _{FE}	75 100	- -	- -
at $-I_C = 150$ mA, $-V_{CE} = 10$ V at $-I_C = 500$ mA, $-V_{CE} = 10$ V	MMBT2907	h _{FE}	100 30	300 -	-
Collector Base Cutoff Current	MMBT2907A	h _{FE}	50	-	-
at -V _{CB} = 50 V	MMBT2907 MMBT2907A	-I _{CBO} -I _{CBO}	-	20 10	nA nA
Collector Base Breakdown Voltage at -I _C = 10 µA		-V _{(BR)CBO}	60	-	V
Collector Emitter Breakdown Voltage at -I _C = 10 mA	MMBT2907 MMBT2907A	-V _{(BR)CEO} -V _{(BR)CEO}	40 60	-	V V
Emitter Base Breakdown Voltage at -I _E = 10 µA		-V _{(BR)EBO}	5	-	V
Collector Saturation Voltage at $-I_C = 150$ mA, $-I_B = 15$ mA at $-I_C = 500$ mA, $-I_B = 50$ mA		-V _{CE(sat)} -V _{CE(sat)}	-	0.4 1.6	V V
Base Saturation Voltage at $-I_C = 150$ mA, $-I_B = 15$ mA at $-I_C = 500$ mA, $-I_B = 50$ mA		$-V_{BE(sat)}$ $-V_{BE(sat)}$		1.3 2.6	V V
Gain Bandwidth Product at $-I_C = 50 \text{ mA}$, $-V_{CE} = 20 \text{ V}$, $f = 100 \text{ MHz}$		f _⊤	200	-	MHz
Collector Output Capacitance at $-V_{CB} = 10 \text{ V}$, f = 1 MHz		C _{ob}	-	8	pF
Turn-on Time at $-V_{CC} = 30 \text{ V}$, $-I_{C} = 150 \text{ mA}$, $-I_{B1} = 15 \text{ mA}$		t _{on}	-	45	ns
Delay Time at $-V_{CC} = 30 \text{ V}$, $-I_{C} = 150 \text{ mA}$, $-I_{B1} = 15 \text{ mA}$		t _d	-	10	ns
Rise Time at $-V_{CC} = 30 \text{ V}$, $-I_{C} = 150 \text{ mA}$, $-I_{B1} = 15 \text{ mA}$		t _r	-	40	ns
Turn-off Time at $-V_{CC} = 6 \text{ V}$, $-I_{C} = 150 \text{ mA}$, $-I_{B1} = -I_{B2} = 150 \text{ mA}$	5 mA	t _{off}	-	100	ns
Storage Time at $-V_{CC} = 6 \text{ V}$, $-I_{C} = 150 \text{ mA}$, $-I_{B1} = -I_{B2} = 150 \text{ mA}$	i mA	t _s	-	80	ns
Fall Time at $-V_{CC} = 6 \text{ V}$, $-I_{C} = 150 \text{ mA}$, $-I_{B1} = -I_{B2} = 150 \text{ mA}$	5 mA	t _f	-	30	ns

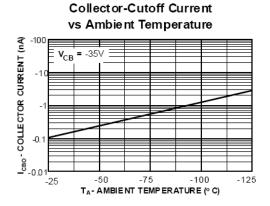
Page 2 of 4

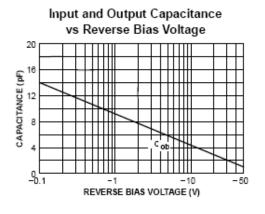


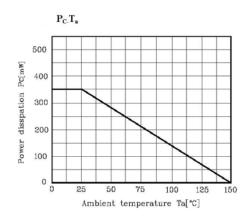










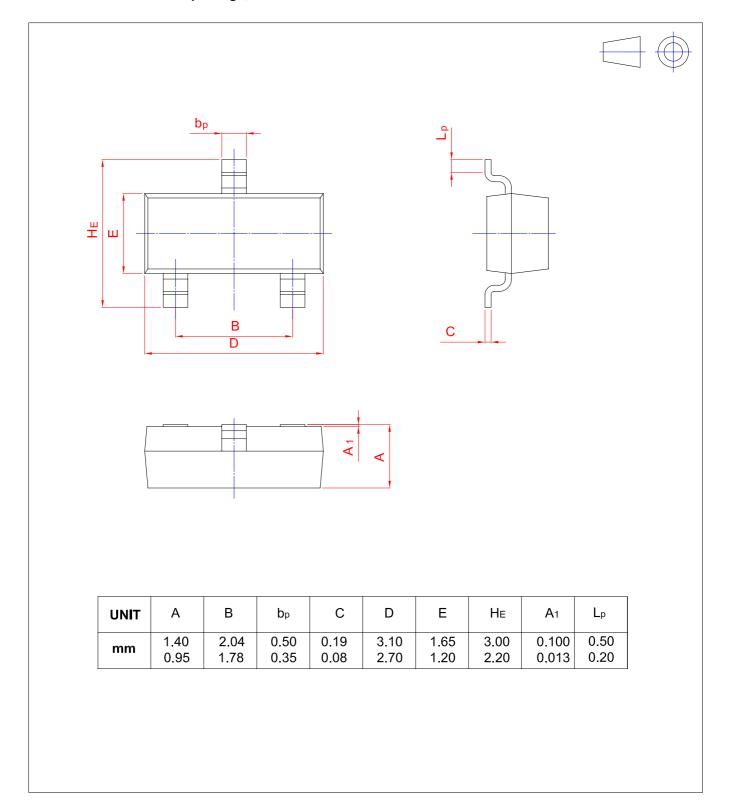


Page 3 of 4

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



Page 4 of 4

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Hong Kong Chuangji manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MMBT-2369-TR BC546/116 BC557/116 BSW67A NJVMJD148T4G NTE123AP-10 NTE153MCP NTE16

NTE195A NTE92 C4460 2N4401-A 2N6728 2SA1419T-TD-H 2SA2126-E 2SB1204S-TL-E 2SC2712S-GR,LF 2SC5488A-TL-H

2SD2150T100R SP000011176 2N2907A 2N3904-NS 2N5769 2SC2412KT146S 2SD1816S-TL-E CPH6501-TL-E MCH4021-TL-E

MJE340 US6T6TR NJL0281DG 732314D CPH3121-TL-E CPH6021-TL-H 873787E IMZ2AT108 UMX21NTR MCH6102-TL-E FP204
TL-E NJL0302DG 2N3583 2SA2014-TD-E 2SC2812-5-TB-E 30A02MH-TL-E NSV40301MZ4T1G NTE13 NTE26 NTE282 NTE323